

VPT Component's Development of Radiation Hardened MOSFETs with LA Semiconductor

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VPT Components has developed a family of radiation hardened silicon power MOSFETs in conjunction with LA Semiconductor. These MOSFETs use a mature, flight proven design and are fully radiation hardened to 100krad(Si) total ionizing dose (TID). Further the MOSFETs are single event gate rupture (SEGR) and single event burnout (SEB) immune at full rated drain potential and zero gate potential using a 15MeV/n xenon (Xe) beam. VPT Components power MOSFETs are also resistant to SEGR and SEB using a 15MeV/n gold (Au) beam when used with a de-rated drain to source bias.